

## P-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- Surface-mounted package
- Advanced trench cell design

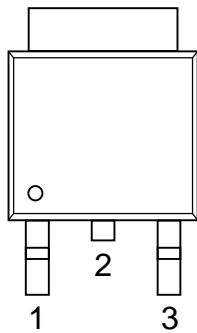
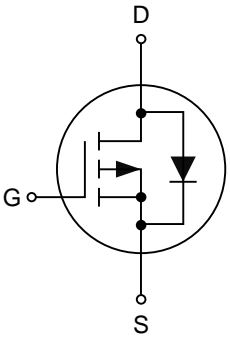
#### 1.2 Applications

- LCD TV appliances
- High power inverter system
- LCDM appliances

#### 1.3 Quick reference

- $BV \geq -100V$
- $R_{DS(ON)} \leq 75m\Omega @ V_{GS} = -10V$
- $P_{tot} \leq 50W$
- $R_{DS(ON)} \leq 90m\Omega @ V_{GS} = -4.5V$
- $I_D \leq -30A$

### 2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)		
2	Drain(D)		
3	Source(S)		

Top View  
TO-252

## 3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	Drain-Source Voltage	T <sub>C</sub> =25°C	-100	-	V
V <sub>GS</sub>	Gate-Source Voltage	T <sub>C</sub> =25°C	-	±20	V
I <sub>D</sub> *	Drain Current (DC)	T <sub>C</sub> =25°C, V <sub>GS</sub> =-10V	-	-30	A
		T <sub>C</sub> =100°C, V <sub>GS</sub> =-10V		-18	A
I <sub>DM</sub> **	Drain Current (Pulsed)	T <sub>C</sub> =25°C, V <sub>GS</sub> =-10V	-	-76	A
P <sub>tot</sub>	Drain power dissipation	T <sub>C</sub> =25°C	-	50	W
T <sub>stg</sub>	Storage Temperature		-55	150	°C
T <sub>J</sub>	Junction Temperature		-	150	°C
I <sub>S</sub>	Continuous-Source Current	T <sub>C</sub> =25°C	-	-30	A
E <sub>AS</sub> *	Single Pulsed Avalanche Energy	V <sub>DD</sub> =-50V, L=1.0mH	-	242	mJ
R <sub>θJA</sub> *	Thermal Resistance-Junction to Ambient		-	50	°C/W
R <sub>θJC</sub> *	Thermal Resistance-Junction to Case		-	2.5	

Notes:

- \* Surface Mounted on 1 in<sup>2</sup> pad area, t ≤ 10 sec
- \*\* Pulse width ≤ 300μs, duty cycle ≤ 2%

## 4. Marking Information

Product Name	Marking
KJ30P10KA	<div style="display: inline-block; border: 1px solid black; padding: 2px;"> <b>30P10A</b>  <b>YWWWXX</b> </div> <b>YWWWXX:</b> Date Code

## 5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ30P10KA	TO-252	-	-	2500	

Note: KUIJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C)

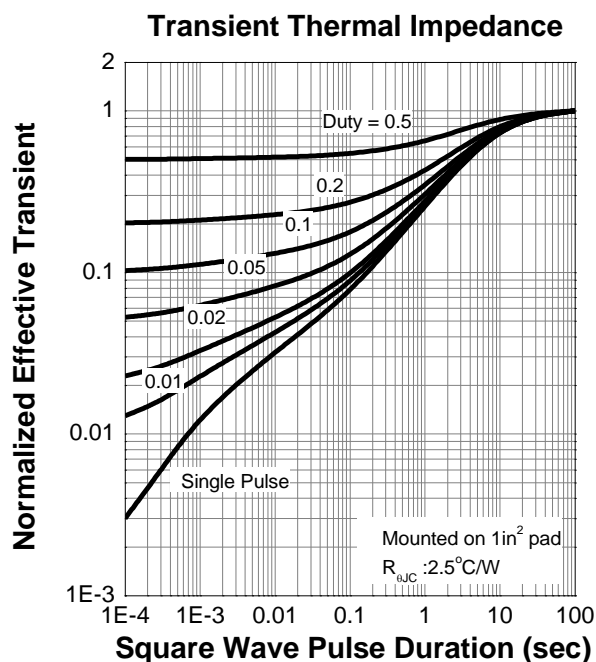
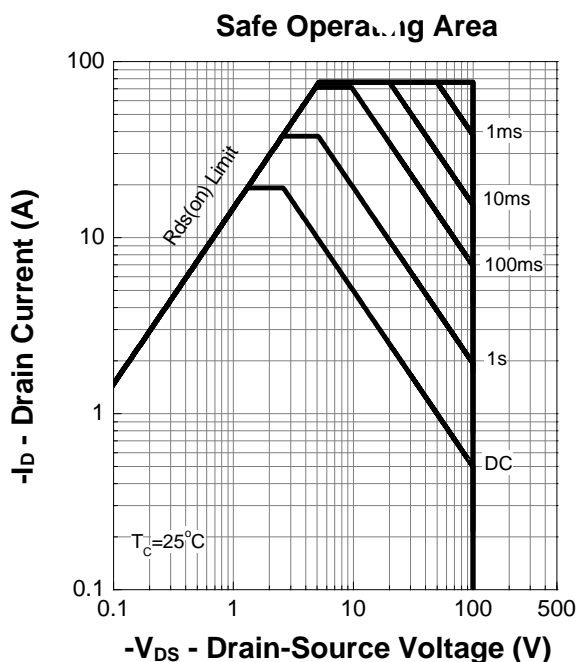
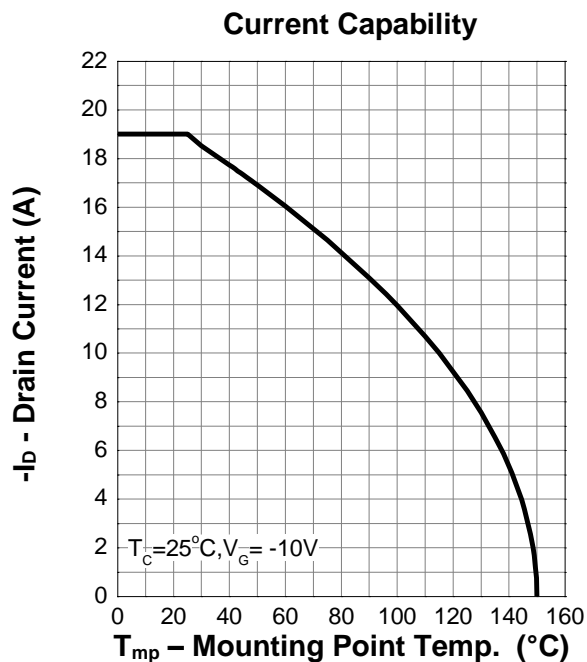
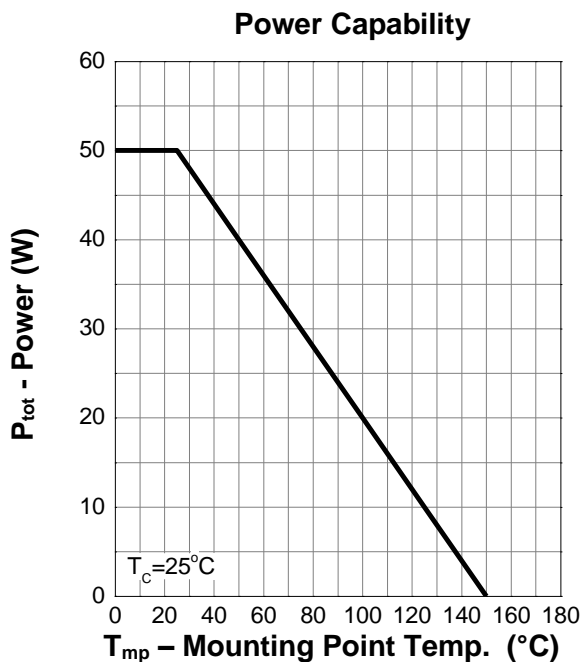
## 6. Electrical Characteristics (T<sub>C</sub>=25°C Unless Otherwise Noted )

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
B <sub>V</sub> DSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>DS</sub> =-250μA	-100	-	-	V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250μA	-1.0	-	-2.4	V
I <sub>DSS</sub>	Drain Leakage Current	V <sub>DS</sub> =-50V, V <sub>GS</sub> =0V	-	-	-1	μA
		T <sub>J</sub> =85°C	-	-	-30	μA
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V	-	-	±100	nA
R <sub>DS(ON)</sub> <sup>a</sup>	On-State Resistance	V <sub>GS</sub> =-10V, I <sub>DS</sub> =-10A	-	68	75	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>DS</sub> =-5A	-	83	90	
<b>Diode Characteristics</b>						
V <sub>SD</sub> <sup>a</sup>	Diode Forward Voltage	I <sub>SD</sub> =-10A, V <sub>GS</sub> =0V	-	-	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>SD</sub> =-10A, dI <sub>SD</sub> /dt=100A/μs	-	32	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	49	-	nC
<b>Dynamic Characteristics<sup>b</sup></b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =-50V Frequency=1MHz	-	2360	-	pF
C <sub>oss</sub>	Output Capacitance		-	81	-	
C <sub>rss</sub>	Reverse Transfer Capacitance		-	67	-	
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =-50V, V <sub>GEN</sub> =-10V, R <sub>G</sub> =4.5Ω, R <sub>L</sub> =5Ω, I <sub>DS</sub> =-10A	-	20	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	22	-	
t <sub>d(off)</sub>	Turn-off Delay Time		-	200	-	
t <sub>f</sub>	Turn-off Fall Time		-	38	-	
<b>Gate Charge Characteristics<sup>b</sup></b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-50V, V <sub>GS</sub> =-10V, I <sub>DS</sub> =-10A	-	71	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	13	-	
Q <sub>gd</sub>	Gate-Drain Charge		-	13	-	

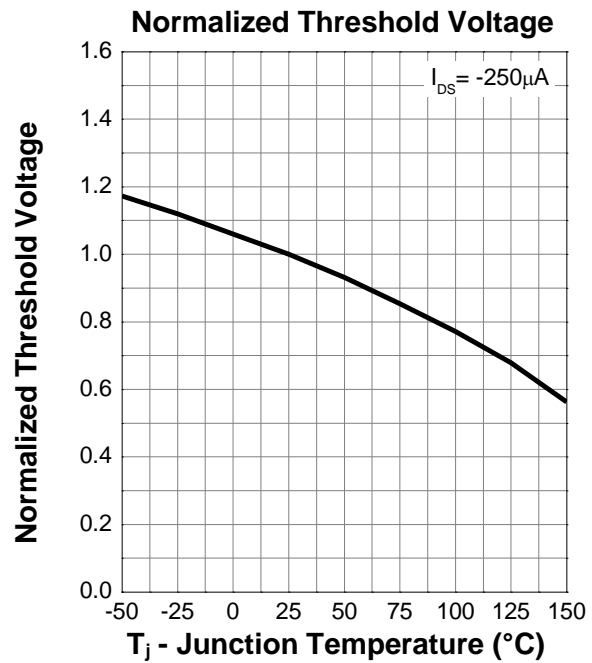
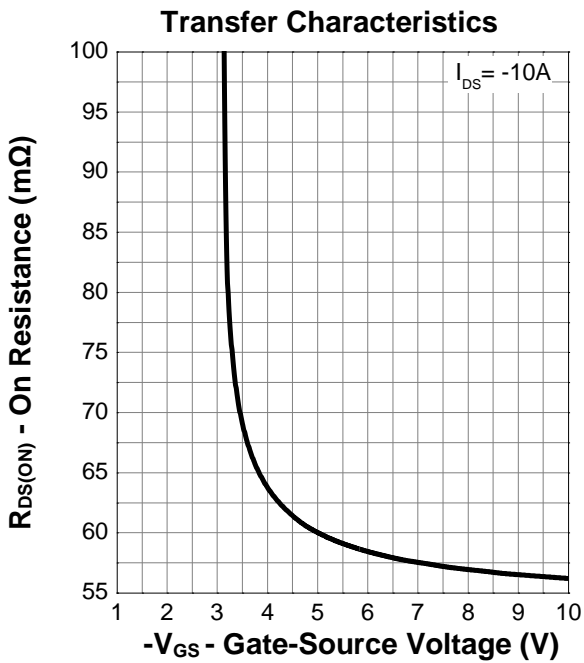
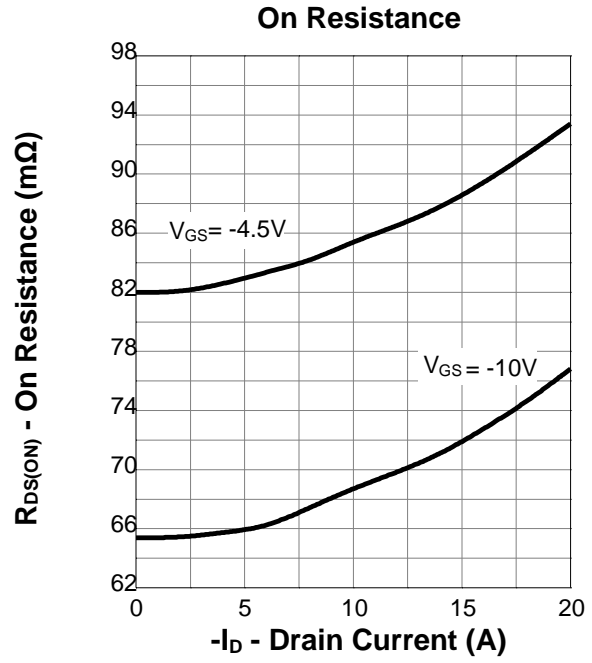
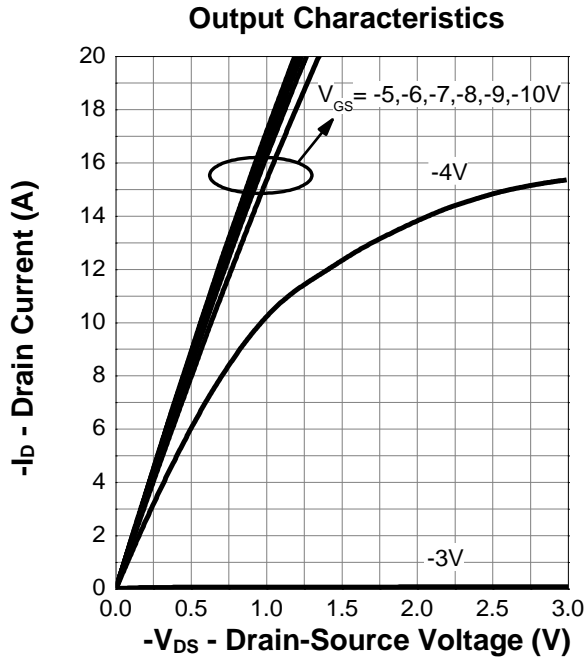
Notes:

- Pulse test; pulse width ≤ 300μs, duty cycle ≤ 2%
- Guaranteed by design, not subject to production testing

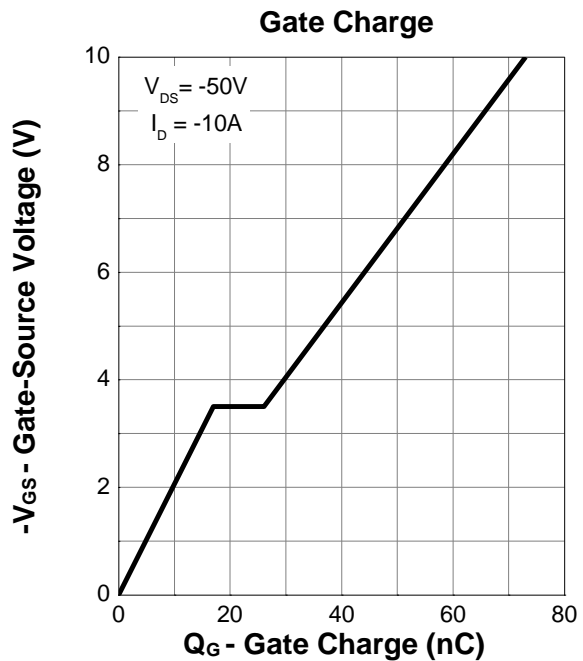
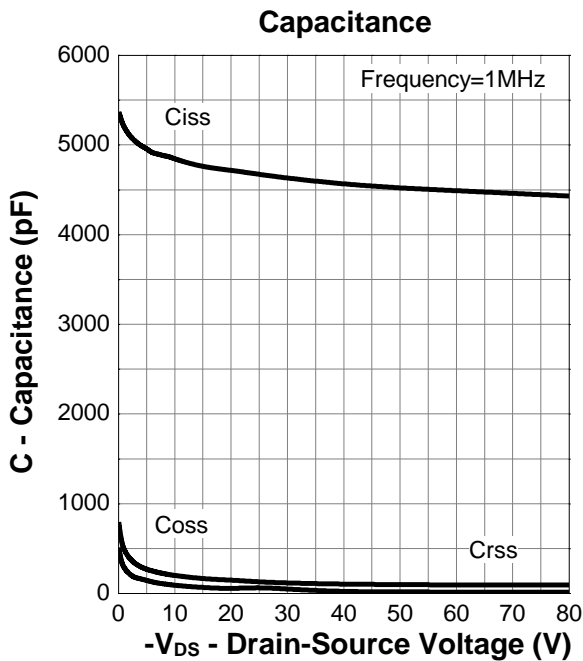
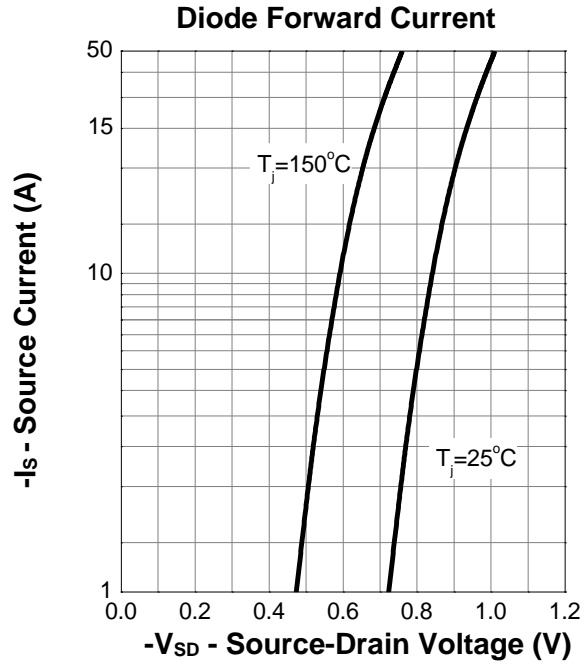
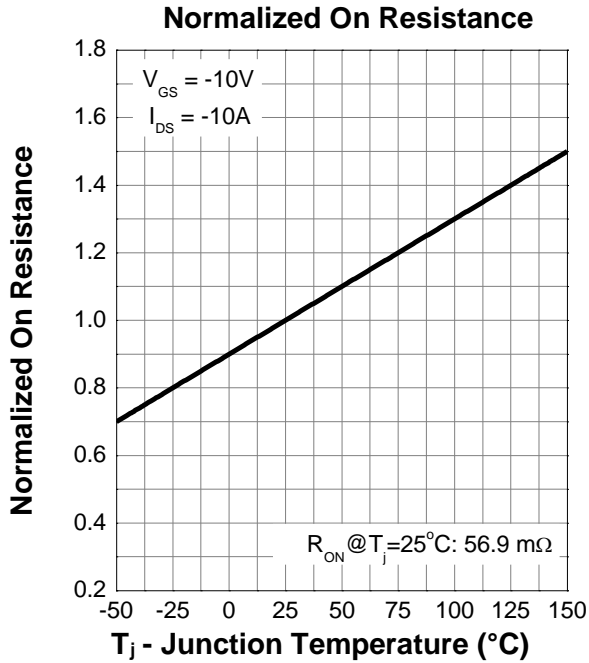
## 7. Typical Characteristics



## 7. Typical Characteristics (cont.)

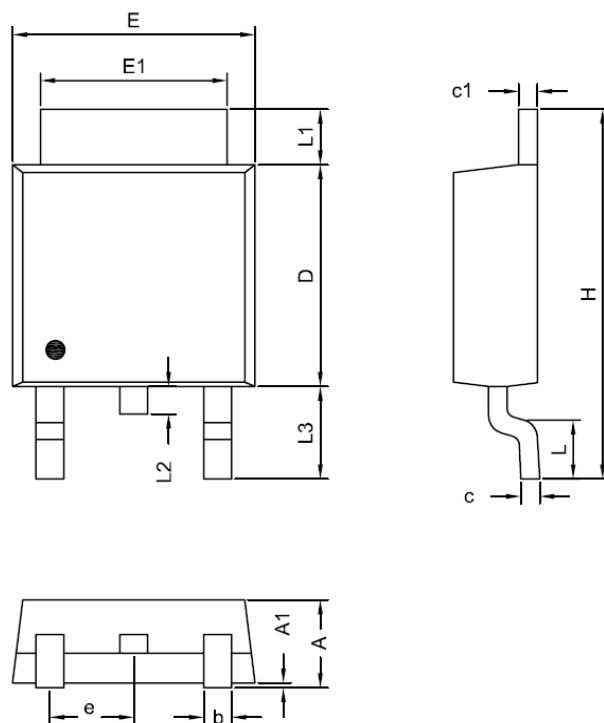


## 7. Typical Characteristics (cont.)



## 8.Package Dimensions

TO-252 Package



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	2.19	2.38
A1	0.02	0.13
D	5.30	6.40
E	6.35	6.80
E1	5.20	5.50
c	0.40	0.60
c1	0.40	0.60
b	0.55	0.85
e	2.30 BCS	
L	1.00	1.80
L1	0.70	1.80
L2	0.70 BCS	
L3	2.40	2.80
H	9.20	10.40